

SECRET

0031 A method and system for reducing acidic contamination on a process wafer following a plasma etching process including; providing an ambient controlled heating chamber for accepting transfer of a process wafer under controlled ambient conditions; transferring the process wafer to the heating chamber under controlled ambient conditions following plasma etching of the process wafer; providing a heat exchange surface within the heating chamber for mounting the process wafer in heat exchange relationship thereto; mounting the process wafer on a heat exchange surface contained within the heating chamber; and, heating the process wafer to a temperature sufficient to vaporize an acidic residue thereon to form acidic vapors; and, removing the acidic vapors from the heating chamber.